

IN THE CLAIMS

1. (Previously Presented) An integrated circuit assembly comprising:
an electronic chip; and
a conductive structure embedded in a material layer having a plurality of vaporization temperatures, the material layer is formed on the electronic chip and the conductive structure includes a horizontal conductive interconnect and at least one vertical wiring via coupling the horizontal conductive interconnect to the electronic chip,
wherein the horizontal conductive interconnect is formed in and above a fill material.
2. (Original) The integrated circuit assembly of claim 1, wherein the electronic chip is a memory chip.
3. (Original) The integrated circuit assembly of claim 2, wherein the memory chip is a dynamic random access memory chip.
4. (Original) The integrated circuit assembly of claim 1, wherein the conductive structure is fabricated from copper.
5. (Original) The integrated circuit assembly of claim 1, wherein at least one of the plurality of vaporization temperatures is about 400 degrees centigrade.
6. (Previously Presented) An integrated circuit assembly comprising:
an electronic chip; and
a conductive structure embedded in a plurality of materials, each of the plurality of materials having a different vaporization temperature, the plurality of materials is formed on the electronic chip and the conductive structure is coupled to the electronic chip;
wherein each of the plurality of materials contacts a surface of the electronic chip.

7. (Canceled)
8. (Previously Presented) The integrated circuit assembly of claim 6, wherein at least one of the plurality of materials is silicon dioxide.
9. (Original) The integrated circuit assembly of claim 6, wherein at least one of the plurality of materials is carbon.
10. (Previously Presented) An integrated circuit assembly comprising:
an electronic chip; and
a conductive structure embedded in a material layer having a structural component having a structural vaporization temperature and a fill material having a vaporization temperature less than the structural vaporization temperature, the material layer is formed on the electronic chip and the conductive structure is coupled to the electronic chip,
wherein the conductive structure includes a horizontal conductive interconnect formed in and above the fill material and at least one vertical wiring via coupling the horizontal conductive interconnect to the electronic chip.
11. (Canceled)
12. (Previously Presented) The integrated circuit assembly of claim 10, wherein the structural component having a structural vaporization temperature is fabricated from silicon dioxide.
13. (Canceled)
14. (Previously Presented) The integrated circuit assembly of claim 10, wherein the fill material is fabricated from carbon.

15. (Withdrawn) The integrated circuit assembly of claim 10, wherein the non-structural component is fabricated from a polymer.

16-17. (Canceled)

18. (Withdrawn) An integrated circuit assembly comprising:
 an electronic chip;
 a support structure mounted on the electronic chip, the support structure having an interstice and a vaporization temperature;
 a material filling the interstice, the material having a vaporization temperature that is less than the vaporization temperature of the support structure;
 a connective structure mounted on the support structure; and
 a conductive structure capable of coupling the electronic chip to the connective structure, the conductive structure embedded in the support structure and the material.

19. (Withdrawn) The integrated circuit assembly of claim 18, wherein the electronic chip is a dynamic random access memory chip.

20. (Withdrawn) The integrated circuit assembly of claim 18, wherein the support structure is fabricated from silicon dioxide.

21. (Withdrawn) The integrated circuit assembly of claim 18, wherein the support structure is a ribbed structure.

22. (Withdrawn) The integrated circuit assembly of claim 18, wherein the material is carbon dioxide.

23. (Withdrawn) The integrated circuit assembly of claim 18, wherein the connective structure is a controlled collapse chip connection (C4) structure.

24-30. (Canceled)

31. (Withdrawn) An integrated circuit assembly comprising:
an electronic chip; and
a post structure mounted on the electronic chip and capable of protecting an air-bridge structure and supporting a C4 structure.

32. (Withdrawn) The integrated circuit assembly of claim 31, wherein the post structure is fabricated from the same material as the air-bridge structure.

33. (Withdrawn) The integrated circuit assembly of claim 31, wherein the post structure is mounted on an insulating base formed on the electronic chip.

34. (Withdrawn) The integrated circuit assembly of claim 31, wherein the post structure is fabricated from an insulator.

35. (Withdrawn) The integrated circuit assembly of claim 31, wherein the insulator is silicon dioxide.

36. (Withdrawn) The integrated circuit assembly of claim 31, wherein the post structure is fabricated from a polymer.

37. (Canceled)

38. (Withdrawn) An integrated circuit assembly comprising:
an electronic chip including a plurality of electronic devices;
a plurality of conductive segments capable of interconnecting the plurality of electronic devices, each of the plurality of conductive segments having a surface area in contact with a material having a dielectric constant of about 1;

a C4 connection coupled to the electronic chip through the plurality of conductive segments; and

a substrate coupled to the C4 connection.

39. (Withdrawn) The integrated circuit assembly of claim 38, wherein the integrated circuit assembly is hermetically sealed.

40. (Withdrawn) The integrated circuit assembly of claim 39, wherein the integrated circuit assembly is back filled with helium.

41. (Withdrawn) The integrated circuit assembly of claim 39, wherein the integrated circuit assembly is back filled with a helium rich gas mixture.

42. (Withdrawn) The integrated circuit assembly of claim 38, wherein the material is air.

43. (Withdrawn) The integrated circuit assembly of claim 38, wherein the material is a foam.

44. (Withdrawn) The integrated circuit assembly of claim 38, further comprising a heat sink coupled to the electronic chip.

45. (Withdrawn) The integrated circuit assembly of claim 44, wherein the integrated circuit assembly is hermetically sealed.

46. (Withdrawn) The integrated circuit assembly of claim 45, wherein the integrated circuit assembly is back filled with helium.

47-74. (Canceled)

75. (Withdrawn) The integrated circuit assembly of claim 6, wherein the electronic chip is an analog signal processing chip.

76. (Withdrawn) The integrated circuit assembly of claim 10, wherein the electronic chip is a digital signal processor.

77. (Withdrawn) The integrated circuit assembly of claim 15, wherein the polymer is a photoresist.

78. (Withdrawn) The integrated circuit assembly of claim 10, wherein the electronic chip is comprised of logic circuits.

79. (Withdrawn) The integrated circuit assembly of claim 18, wherein the conductive structure is fabricated from a copper alloy.

80. (Withdrawn) An integrated circuit assembly comprising:
an electronic chip; and
a conductive structure including a support structure, the conductive structure having a vaporization temperature and the conductive structure including the support structure is embedded in a material layer having a vaporization temperature less than the vaporization temperature of the conductive structure, the material layer is formed on the electronic chip and the conductive structure is coupled to the electronic chip.

81. (Withdrawn) The integrated circuit assembly of claim 25, wherein the electronic chip is a microprocessor.

82. (Withdrawn) An integrated circuit memory device comprising:
an electronic memory chip; and
a ribbed structure mounted on the electronic memory chip and capable of protecting an air-bridge structure and supporting a C4 structure.

83. (Withdrawn) The integrated circuit assembly of claim 27, wherein the ribbed structure is fabricated from an inorganic insulator.

84. (Withdrawn) The integrated circuit assembly of claim 27, wherein the ribbed structure is fabricated from an organic material.

85. (Withdrawn) The integrated circuit assembly of claim 27, wherein the ribbed structure is fabricated from of a mix of organic and inorganic materials.

86. (Withdrawn) The integrated circuit assembly of claim 36, wherein the polymer is polyimide.

87. (Withdrawn) A computer system comprising:
a processor;
a memory device having a plurality of circuit devices, the memory device coupled to the processor; and
an air-bridge structure and a support structure fabricated on the memory device, the air-bridge structure capable of coupling at least two of the plurality of circuit devices and the support structure capable of supporting the memory device mounted as a flip chip.

88. (Withdrawn) The computer system of claim 47, wherein the air-bridge structure is embedded in a dielectric having a dielectric constant of about 1.

89. (Withdrawn) The computer system of claim 47, wherein the support structure fabricated on the memory device is a ribbed support structure.

90. (Withdrawn) An integrated circuit assembly comprising:
an electronic chip;
a material layer having a plurality of vaporization temperatures, wherein the material layer includes a support structure having a number of support members that are approximately the length of one of the sides of the electronic chip; and
a conductive structure embedded in the material layer, the material layer is formed on the electronic chip and the conductive structure is coupled to the electronic chip.

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91. (Withdrawn) An integrated circuit assembly comprising:
- an electronic chip;
 - a plurality of material that includes a support structure having a number of support members that are approximately parallel to one of the sides of the electronic chip; and
 - a conductive structure embedded in the plurality of materials, each of the plurality of materials having a different vaporization temperature, the plurality of materials is formed on the electronic chip and the conductive structure is coupled to the electronic chip.
92. (Withdrawn) An integrated circuit assembly comprising:
- an electronic chip;
 - a conductive structure embedded in a material layer having a structural component having a structural vaporization temperature and a non-structural component having a non-structural vaporization temperature less than the structural vaporization temperature, wherein the structure component has a number of support members that are approximately the length of one of the sides of the electronic chip and are approximately parallel to one of the sides of the electronic chip, wherein the number of support members are arranged to create a number of interstices.
93. (Withdrawn) An integrated circuit assembly comprising:
- an electronic chip;
 - a ribbed support structure mounted on the electronic chip, the ribbed support structure having a vaporization temperature, wherein the ribbed support structure comprises a number of support members, wherein the number of support members are parallel to one of the sides of the electronic chip and are approximately the length of the electronic chip, the number of support members arranged to create an interstice;
 - a material filling the interstice, the material having a vaporization temperature that is less than the vaporization temperature of the ribbed support structure;
 - a controlled collapse chip connection (C4) connective structure mounted on the ribbed support structure, wherein the C4 structure is to mount on a silicon substrate; and

a conductive structure capable of coupling the electronic chip to the connective structure, the conductive structure embedded in the ribbed support structure and the material.

94. (Previously Presented) The integrated circuit assembly of claim 1, wherein the electronic chip is a flip chip.